⟨Transistor⟩

2SC5384

For High Frequency Amplify, Medium Frequency Amplify Application Silicon NPN Epitaxial Type Uitra Super Mini

③: Collector

Note)

DESCRIPTION

SC5384 is a super mini silicon NPN epitaxial type transistor designed for high frequency amplify, oscillating, frequency exchange, medium frequency amplify application.

FEATURE

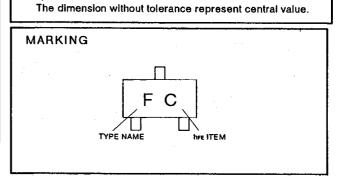
- · High gain (@10.7MHz), MAG=45dB typ
- · Low noise (@10.7MHz), NF=3.0dB typ
- · Small yre (@10.7MHz), yre=-J0.11mS typ
- · Super mini package for easy mounting

APPLICATION

High frequency amplify, oscillating, frequency exchange, medium frequency amplify for small comunication machine, FM/AM radio.

MAXIMUM RATINGS (Ta=25°C)

SYMBOL	PARAMETER	RATINGS	UNIT
Vсво	Collector to Base voltage	30	٧
Vebo	Emitter to Base voltage	4	٧
VCEO	VCEO Collector to Emitter voltage		٧
<u> </u>	Collector current	30	mΑ
Pc	Collector dissipation (Ta=25℃)	125	mW
Tj	Junction temperature	+125	°C
Tstg	Tstg Storage temperature		°C



JEDEC: -

ELECTRICAL CHARACTERISTICS (Ta=25°C)

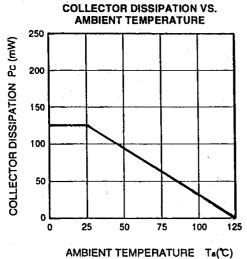
SYMBOL	PARAMETER	TESTCONDITIONS	LIMITS			
			MIN	TYP	MAX	TINU
Ісво	Collector cut off current	VcB=25V, I E=0			1	μΑ
l EBO	Emitter cut off current	VEB=4V, I C=0			1	μΑ
hFE *	DC forward current gain	VcE=6V, 1 c=1mA	35		180	 -
VCE(sat)	C to E saturation voltage	I c=10mA, I B=1mA		0.1	0.3	V
fT	Gain band width product	VcE=6V, I E=-1mA	150	200		MHz
Соь	Collector output capacitance	VcB=6V, I E=0, f=1MHz		2.0	2.7	pF
Ccrb'b	Base time constant	VcB=6V, I E=-1mA, f=31.8MHz		20	60	pS
NF	Noise figure	VCE=6V, I E=-1mA, f=10.7MHz, RG= 500Ω		3.0		dB

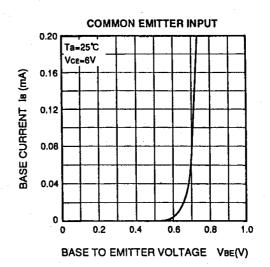
ITEM	В	С	D
hFE	35~70	55~110	90~180

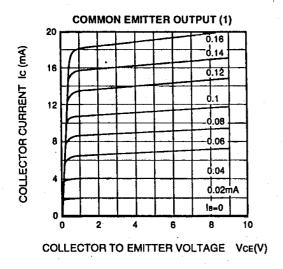
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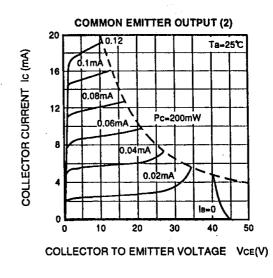
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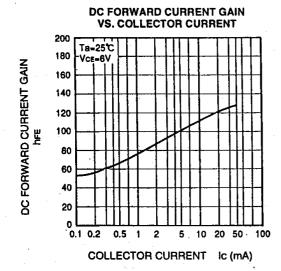
TYPICAL CHARACTERISTICS

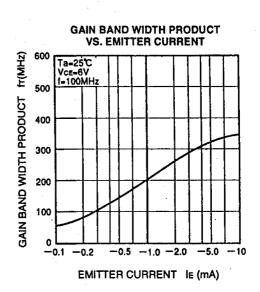












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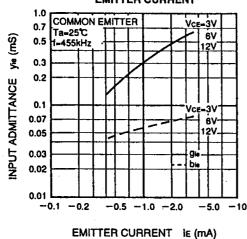
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COMMON EMITTER, y PARAMETER (TYPICAL VALUE)

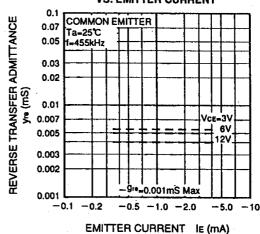
Te: y Paramet	st conditions ter	f=455kHz VCE=6V fe= — 1 mA	f=1MHz VcE=6V IE=−1mA	f=10.7MHz VcE=6V IE= - 1mA	f=100MHz Vce=6V Ie= — 1 mA
yie (mS)	gie	0.30	0.30	0.38	4.4
	bie	0.06	0.12	1.40	11.0
yre (mS)	gre	0.001Max	0.001Max	0.005Max	0.05Max
	-bre	0.005	0.010	0.11	1.0
yle (mS)	gte .	50	46	37	25 ,
	bte	1.0Max	1.0Max	2.8	16
yoe (mS)	goe	0.010	0.012	0.03	0.32
	boe	0.011	0.022	0.18	1.3

COMMON EMITTER, 455kHz y PARAMETER

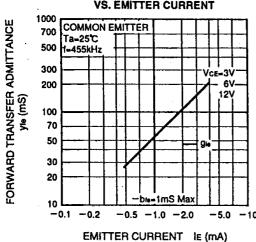




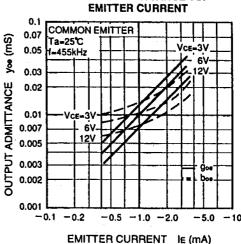
REVERSE TRANSFER ADMITTANCE VS. EMITTER CURRENT



FORWARD TRANSFER ADMITTANCE VS. EMITTER CURRENT



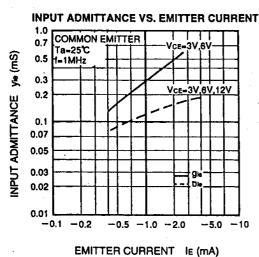
OUTPUT ADMITTANCE VS.



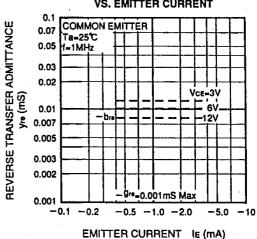
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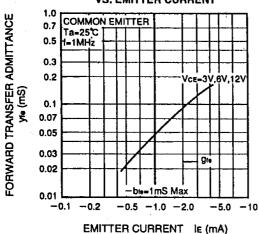
COMMON EMITTER, 1MHz y PARAMETER



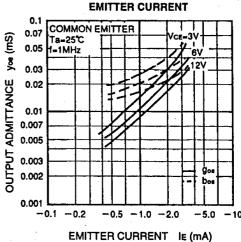
REVERSE TRANSFER ADMITTANCE VS. EMITTER CURRENT



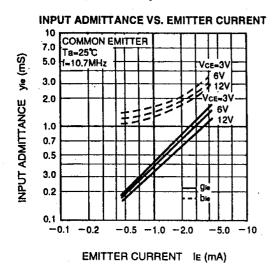
FORWARD TRANSFER ADMITTANCE VS. EMITTER CURRENT



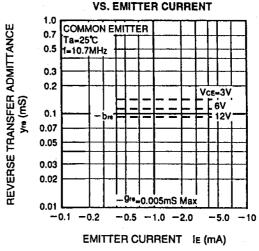
OUTPUT ADMITTANCE VS.



COMMON EMITTER, 10.7MHz y PARAMETER

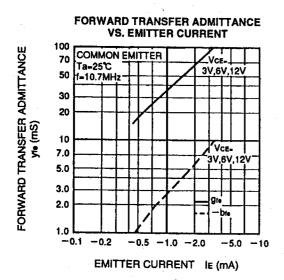


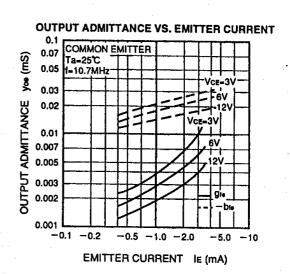
REVERSE TRANSFER ADMITTANCE VS. EMITTER CURRENT



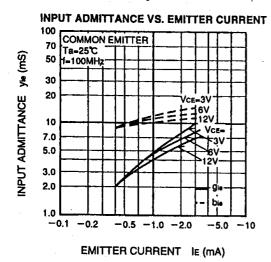
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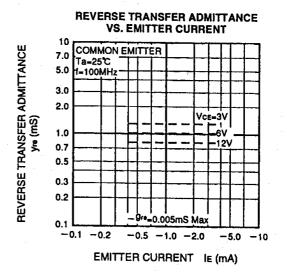
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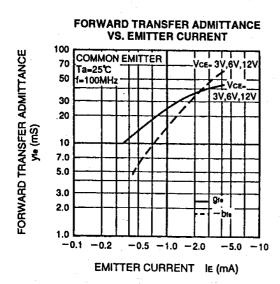


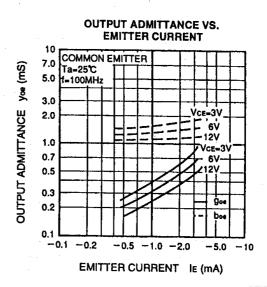


COMMON EMITTER, 100MHz y PARAMETER











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